

REMARKS

Claims 1-4, 6, and 8-10 are pending in the subject application. Independent claim 1 has been amended by the present amendment. The amendment is fully supported by the application as originally filed (see, e.g., specification at page 12, lines 5-9 and 19-24; page 13, lines 6-11; page 19, lines 3-6; and FIGS. 1 and 5).

Claims 1-4, 6, and 8-10 were rejected under 35 USC 112, first paragraph "because the specification, while being enabling for CO₂ laser, does not reasonably provide enablement for all carbon gas laser" (see Office Action of 11/06/2007 at page 2, paragraph #2).

Independent claim 1 has been amended to replace "carbon gas laser light" with "carbon dioxide gas laser light," as described on page 13, lines 6-11 of the specification, to overcome the rejection under 35 USC 112, first paragraph. Withdrawal of the rejection is respectfully requested.

Claims 1-4, 6, and 8-10 were rejected under 35 USC 112, first paragraph for lack of enablement, and under 35 USC 112, second paragraph as being indefinite, because of the phrase "a solid-state laser light selected from the group comprising excimer laser light" in claim 1.

Independent claim 1 has been amended to recite that the first laser light is "excimer laser light or YAG laser light," as described on page 12, lines 5-9 of the specification. It is believed that the amendment to claim 1 overcomes the rejections under 35 USC 112, first and second paragraphs.

Claims 1-3, 6, 8, and 10 were rejected under 35 USC 103(a) as being obvious over U.S. Patent Application Publication US 2003/0021307 to Yamazaki (hereinafter "the '307 publication") in view of U.S. Patent Application Publication US 2002/0094613 to Yamazaki et al. (hereinafter "the '613 publication"). Claims 4 and 9 were rejected over combinations including the above references. These rejections are respectfully traversed.

Independent claim 1 recites a crystal growth apparatus, including: first radiation means for radiating first laser light, which is excimer laser light or YAG laser light, for melting a semiconductor thin film; and second radiation means for radiating second laser light, which is carbon dioxide gas laser light, for heating a base material without melting the base material. As recited in independent claim 1, the first radiation means includes a mask having a plurality of slits, and image forming means for forming on the semiconductor thin film an image of the first laser light transmitted through the mask.

The proposed combination of the '307 publication in view of the '613 publication does not teach or suggest a crystal growth apparatus in which a first radiation means includes "a mask having a plurality of slits for transmitting the first laser light, and image forming means for forming on the semiconductor thin film an image of the first laser light transmitted through the slits as an image of the mask," as recited in independent claim 1.

Further, there is no teaching or suggestion in the proposed combination of the '307 publication in view of the '613 publication of a crystal growth apparatus that uses excimer laser light or YAG laser light to melt a semiconductor thin film, and carbon dioxide gas laser light to heat without melting a base material.

It is believed the application is in condition for immediate allowance, which action is earnestly solicited.

Respectfully submitted,

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